

Advanced PECVD-Nitride2(HF n=2.00, 9.3nm/min)				Advanced PECVD SiN 3000A Typical Film Properties
SiN deposition~3000A, 300C				Deposition rate=9.05nm/min
Step1: NITRIDE2 coat				Refractive index@632.8nm=1.952
	Name	Value	Changeable	Stress=-480.68MPa
	Process pressure	800 mtorr	N	HF etch rate=48.32nm/min
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	10	Y	
	step time(s)	0	Y	
	2%SiH4 %He	1040	N	
	N2	980	N	
	NH3	17	N	
Step2: NITRIDE2 deposition				
	Name	Value	Changeable	
	Process pressure	800 mtorr	N	
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	30	Y	
	step time(s)	0	Y	
	2%SiH4 %He	1040	N	
	N2	980	N	
	NH3	17	N	
Step3: STANDARD PLASMA CLEAN				
1. pump down				
	Name	Value	Changeable	
	stabilization time	15 seconds	N	
	step time(m)	0	N	
	step time(s)	30	N	
2. Pre-purge				
	Name	Value	Changeable	
	purge	1 (Yes/No)	N	
	stabilization time	15 seconds	N	
	step time(m)	1	N	
	step time(sec)	0	N	
3.1 High Pressure				
	Name	Value	Changeable	
	Clod position	50%	N	
	Ctune position	50%	N	
	DriveMatch	1 (Yes/No)	N	
	Process pressure	600 mtorr	N	
	RF setpoint=300	300 W	N	
	Stabilization time	35 seconds	N	
	step time(m)	ENTER TIME	Y	For 7min(coat+deposition) run 1min CLEAN
	step time(s)	0	Y	
	CF4/O2(5)	500 sccm	N	